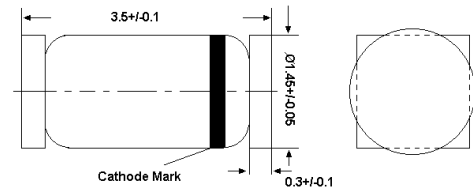


LS4448

Silicon Epitaxial Planar Switching Diode

Fast switching diode in QuadroMELF case especially suited for automatic surface mounting. Identical electrically to standard JEDEC 1N4448.

LS-34



QuadroMELF
Dimensions in mm

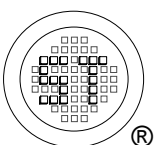
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current at $t < 1$ s	I_{FSM}	500	mA
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_J	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5$ mA at $I_F = 100$ mA	V_F	0.62 -	0.72 1	V
Reverse Current at $V_R = 20$ V at $V_R = 75$ V	I_R	- -	25 5	nA μA
Reverse Breakdown Voltage tested with 100 μA Pulses	$V_{(BR)R}$	100	-	V
Capacitance at $V_R = 0$, $f = 1$ MHz	C_{tot}	-	4	pF
Reverse Recovery Time at $I_F = 10$ mA to $I_R = 1$ mA, $V_R = 6$ V, $R_L = 100 \Omega$	t_{rr}	-	4	ns



SEMTECH ELECTRONICS LTD.
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